

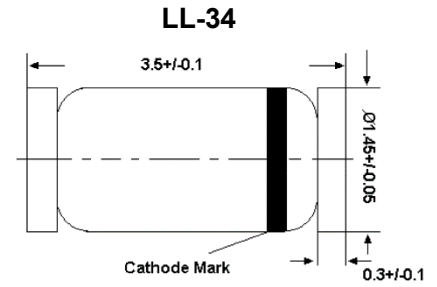


ZMM5B1

Silicon Epitaxial Planar Zener Diodes

Features

MiniMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 55 to + 175	$^\circ\text{C}$

Characteristics at $T_A = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300	$^\circ\text{C/W}$

Electrical Characteristics at $T_A = 25^\circ\text{C}$

Type	Zener Voltage Range			Dynamic Resistance			Reverse Leakage Current			Temp coefficient of Zener Voltage
	$V_{Z\text{nom}}$ V	I_{ZT} for V_{ZT} ^{Note1}		r_{ZJT} Ω	r_{ZJK} at I_{ZK} Ω	I_{ZK} mA	$T_a = 25^\circ\text{C}$		I_R at V_R V	TKvz %/K
		mA	V				μA	μA		
ZMM 5B1	5.1	5	4.99...5.20	<35	<5	1	<0.1	<2	1	-0.02...+0.02

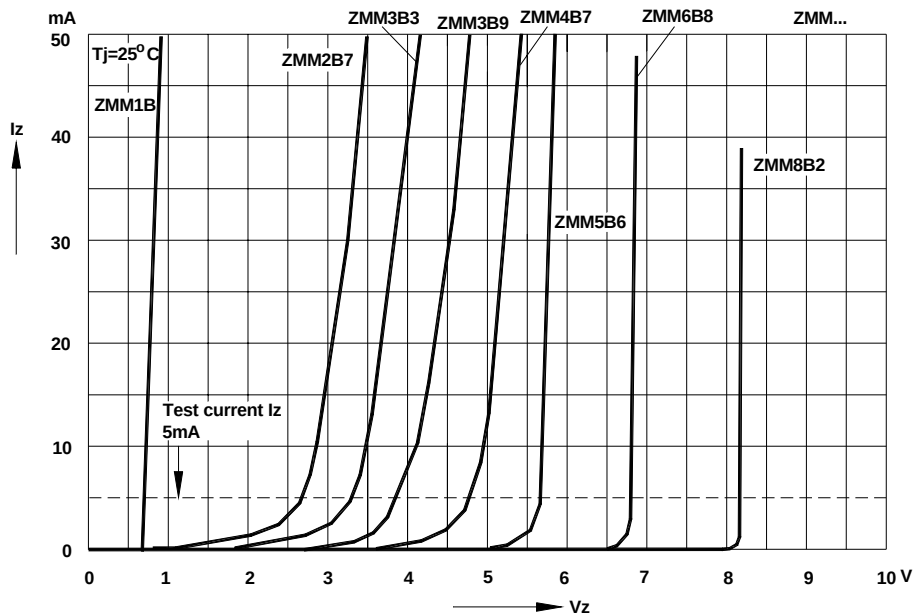
Note1: $V_Z > 4.8\text{V}$ @ $I_Z = 0.5\text{mA}$



Electrical Characteristics Curves

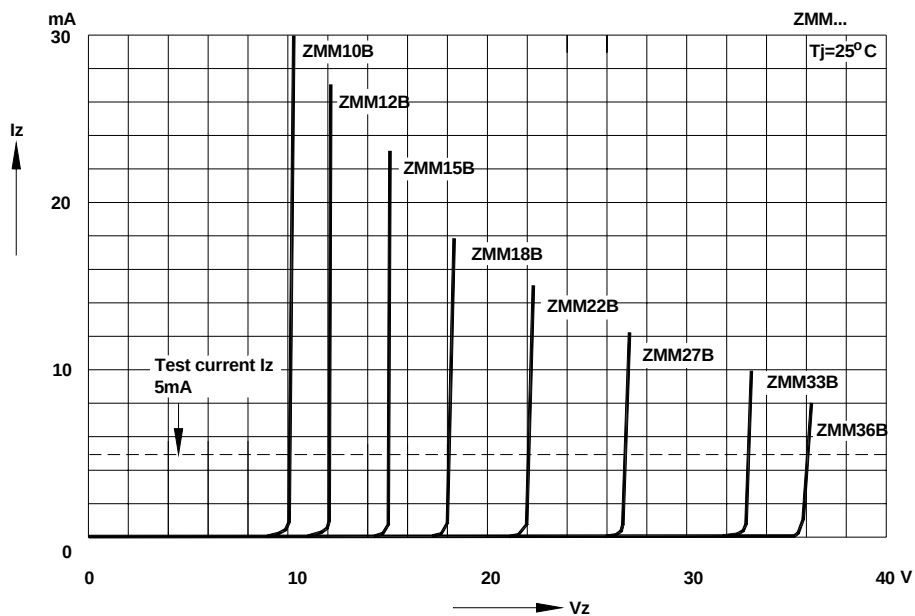
Breakdown characteristics

$T_j = \text{constant}$ (pulsed)



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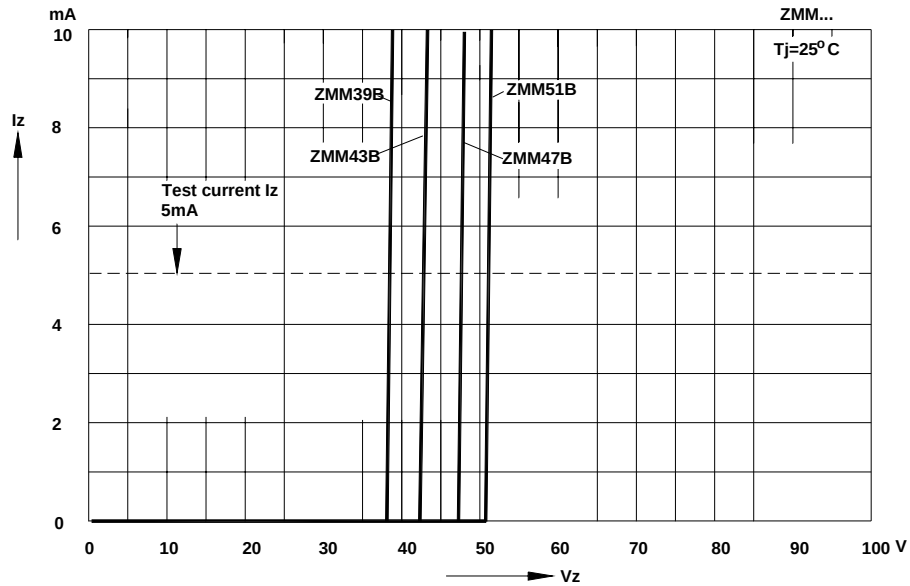




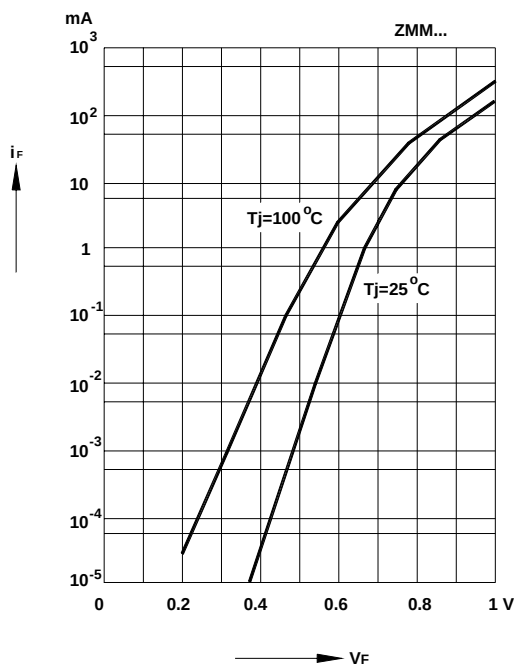
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Breakdown characteristics
 $T_j = \text{constant (pulsed)}$



Forward characteristics



Admissible power dissipation versus ambient temperature
Valid provided that electrodes are kept at ambient temperature.

